Slotted Optical Switch

OPB660N

Obsolete (OPB660T)

Electronics

Features:

- Non-contact switching
- Printed circuit board mounting
- Enhanced signal to noise ratio
- Gap 0.125" (3.18 mm) wide and 0.345" (8.76 mm) deep slot
- Emitter Aperture 0.05" X 0.06" (1.27 mm X 1.52 mm)
- Sensor Aperture 0.01" X 0.06" (0.25 mm X 1.52 mm)

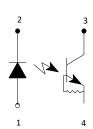
Description:

The OPB660N slotted optical switch consists of an infrared emitting diode and a NPN silicon phototransistor, combined with an enhanced low current roll-off that improves contrast ratio and provides immunity to background irradiance. Housings are made from an opaque grade of injection-molded plastic to minimize sensitivity to both visible and near-infrared light.

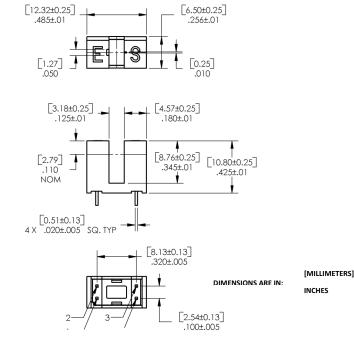
Applications:

- Non-contact transmissive object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

Part Number	LED Peak Wavelength	Sensor	Slot Width / Depth	Aperture Emitter/Sensor	Lead Length / Spacing
OPB660N	000	Rbe	0.43511 / 0.24511	0.05 / 0.04	0.100" / 0.320"
OPB660T Obsolete	890 nm	Transistor	0.125" / 0.345"	0.05" / 0.01"	(MIN)



Pin #	LED	Pin #	Transistor
1	Anode	3	Collector
2	Cathode	4	Emitter





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Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage & Operating Temperature Range	-40° C to +100° C	
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. with soldering iron] (1)	260° C	
put Diode		
Forward DC Current	50 mA	
Peak Forward Current (1 μs pulse width, 300 pps)	1 A	
Reverse DC Voltage	3 V	
Power Dissipation ⁽²⁾	100 mW	
Output Phototransistor		
Collector-Emitter Voltage	24 V	
Collector DC Current	30 mA	
Power Dissipation ⁽³⁾	200 mW	

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER		TYP	MAX	UNITS	TEST CONDITIONS	
Input Diode							
V_{F}	Forward Voltage	-	1	1.6	V	I _F = 10 mA	
I _R	Reverse Current		-	100	μΑ	V _R = 3 V	
Output Phototransistor							
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	24	-	-	V	Ι _{CE} = 100 μΑ	
BV _{ECO}	Emitter Reverse Breakdown Voltage	0.4	1	1	V	Ι _{ΕC} = 100 μΑ	
I _{CEO}	Collector-Emitter Dark Current	-	1	100	μΑ	V _{CE} = 5 V	
Combined							
V_{SAT}	Collector-Emitter Saturation Voltage	-	-	0.4	V	$I_F = 10$ mA, $I_C = 100$ μ A, (gap unblocked)	
I _{C(ON)}	On-State Collector Current	600	-	-	μΑ	I _F = 10 mA, V _{CE} = 5 V	

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum of 20 grams force may be applied to leads when soldering.
- (2) Derate linearly 1.33 mW/° C above 25° C.
- (3) Derate linearly 2.0 mW/° C above 25° C.

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Performance

